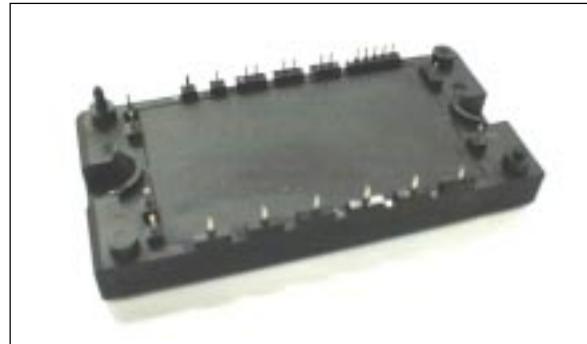


## PIM/Built-in converter with thyristor and brake (S series) 600V / 50A / PIM



### ■ Features

- Low  $V_{CE(sat)}$
- Compact Package
- P.C. Board Mount Module
- Converter Diode Bridge Dynamic Brake Circuit

### ■ Applications

- Inverter for Motor Drive
- AC and DC Servo Drive Amplifier
- Uninterruptible Power Supply

### ■ Maximum ratings and characteristics

● Absolute maximum ratings ( $T_c=25^\circ\text{C}$  unless without specified)

Item	Symbol	Condition	Rating	Unit	
Inverter	Collector-Emitter voltage	$V_{CES}$	600	V	
	Gate-Emitter voltage	$V_{GES}$	$\pm 20$	V	
	Collector current	$I_C$	Continuous	50	A
		$I_{CP}$	1ms	100	A
		$-I_C$		50	A
	Collector power dissipation	$P_C$	1 device	200	W
Brake	Collector-Emitter voltage	$V_{CES}$	600	V	
	Gate-Emitter voltage	$V_{GES}$	$\pm 20$	V	
	Collector current	$I_C$	Continuous	30	A
		$I_{CP}$	1ms	60	A
	Collector power dissipation	$P_C$	1 device	120	W
	Repetitive peak reverse voltage(Diode)	$V_{RRM}$		600	V
Thyristor	Repetitive peak off-state voltage	$V_{DRM}$		800	V
	Repetitive peak reverse voltage	$V_{RRM}$		800	V
	Average on-state current	$I_T(AV)$	50Hz/60Hz sine wave	50	A
	Surge On-state current (Non-Repetitive)	$I_{TSM}$	$T_j=125^\circ\text{C}$ , 10ms half sine wave	563	A
	Junction temperature	$T_{jw}$		125	$^\circ\text{C}$
	Repetitive peak reverse voltage	$V_{RRM}$		800	V
Converter	Average output current	$I_O$	50Hz/60Hz sine wave	50	A
	Surge current (Non-Repetitive)	$I_{FSM}$	$T_j=150^\circ\text{C}$ , 10ms	525	A
	$I^2t$ (Non-Repetitive)	$I^2t$	half sine wave	1378	$\text{A}^2\text{s}$
	Junction temperature (except Thyristor)	$T_j$		+150	$^\circ\text{C}$
Storage temperature	$T_{stg}$			-40 to +125	$^\circ\text{C}$
Isolation between terminal and copper base *2	$V_{iso}$	AC : 1 minute	AC 2500	V	
voltage between thermistor and others *3			AC 2500	V	
Mounting screw torque			1.7 *1	N·m	

\*1 Recommendable value : 1.3 to 1.7 N·m (M4)

\*2 All terminals should be connected together when isolation test will be done.

\*3 Terminal 8 and 9 should be connected together. Terminal 1 to 7 and 10 to 26

should be connected together and shorted to copper base.

● Electrical characteristics (T<sub>j</sub>=25°C unless otherwise specified)

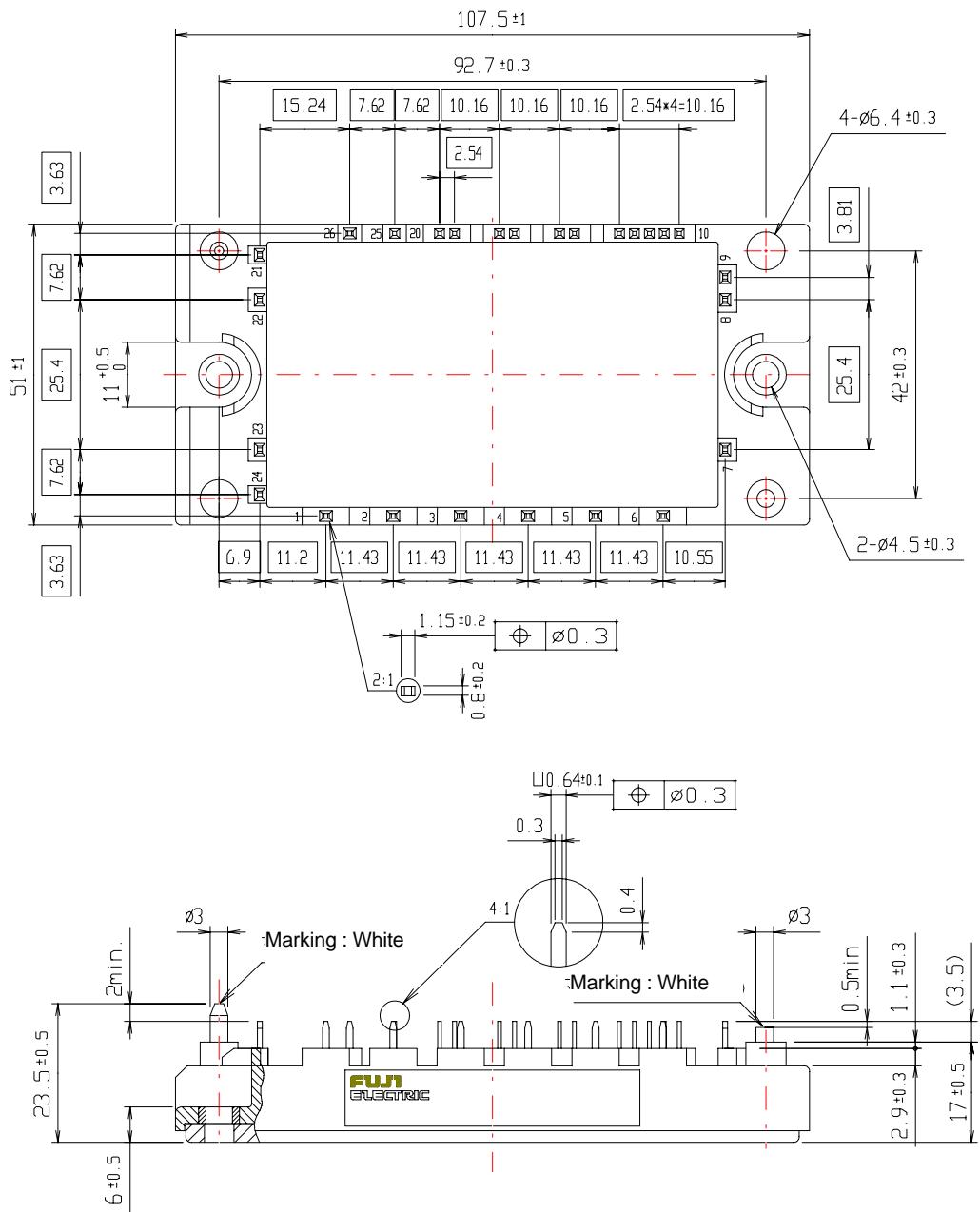
Item	Symbol	Condition	Characteristics			Unit	
			Min.	Typ.	Max.		
Inverter	Zero gate voltage collector current	I <sub>CES</sub>	V <sub>CE</sub> =600V, V <sub>GE</sub> =0V			150	μA
	Gate-Emitter leakage current	I <sub>GES</sub>	V <sub>CE</sub> =0V, V <sub>GE</sub> =±20V			200	nA
	Gate-Emitter threshold voltage	V <sub>GE(th)</sub>	V <sub>CE</sub> =20V, I <sub>c</sub> =50mA	5.5	7.8	8.5	V
	Collector-Emitter saturation voltage	V <sub>CE(sat)</sub>	V <sub>GE</sub> =15V, I <sub>c</sub> =50A	chip	1.8		V
				terminal	1.95	2.4	
	Input capacitance	C <sub>ies</sub>	V <sub>GE</sub> =0V, V <sub>CE</sub> =10V, f=1MHz		5000		pF
	Turn-on time	t <sub>on</sub>	V <sub>CC</sub> =300V		0.45	1.2	μs
		t <sub>r</sub>	I <sub>c</sub> =50A		0.25	0.6	
	Turn-off	t <sub>off</sub>	V <sub>GE</sub> =±15V		0.40	1.0	
		t <sub>f</sub>	R <sub>G</sub> =51Ω		0.05	0.35	
Brake	Forward on voltage	V <sub>F</sub>	I <sub>F</sub> =50A	chip	1.75		V
				terminal	1.9	2.6	
	Reverse recovery time of FRD	t <sub>rr</sub>	I <sub>F</sub> =50A			300	ns
	Zero gate voltage collector current	I <sub>CES</sub>	V <sub>CES</sub> =600V, V <sub>GE</sub> =0V			150	μA
	Gate-Emitter leakage current	I <sub>GES</sub>	V <sub>CE</sub> =0V, V <sub>GE</sub> =±20V			200	nA
	Collector-Emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>c</sub> =30A, V <sub>GE</sub> =15V	chip	1.8		V
				terminal	1.95	2.4	
	Turn-on time	t <sub>on</sub>	V <sub>CC</sub> =300V		0.45	1.2	μs
		t <sub>r</sub>	I <sub>c</sub> =30A		0.25	0.6	
	Turn-off time	t <sub>off</sub>	V <sub>GE</sub> =±15V		0.40	1.0	
		t <sub>f</sub>	R <sub>G</sub> =82Ω		0.05	0.35	
Thyristor	Reverse current	I <sub>RRM</sub>	V <sub>R</sub> =600V			150	μA
	off-state current	I <sub>DM</sub>	V <sub>DM</sub> =800V			1.0	mA
	Reverse current	I <sub>RRM</sub>	V <sub>RM</sub> =800V			1.0	mA
	Gate trigger current	I <sub>GT</sub>	V <sub>D</sub> =6V, I <sub>t</sub> =1A			100	mA
	Gate trigger voltage	V <sub>GT</sub>	V <sub>D</sub> =6V, I <sub>t</sub> =1A			2.5	V
Converter	On-state voltage	V <sub>TM</sub>	I <sub>TM</sub> =50A	chip	1.1	1.3	V
				terminal	1.2		
	Forward on voltage	V <sub>FM</sub>	I <sub>F</sub> =50A	chip	1.1		V
				terminal	1.2	1.5	
Thermistor	Reverse current	I <sub>RRM</sub>	V <sub>R</sub> =800V			150	μA
	Resistance	R	T=25°C		5000		Ω
			T=100°C	465	495	520	
B value	B		T=25/50°C	3305	3375	3450	K

## ● Thermal resistance Characteristics

Item	Symbol	Condition	Characteristics			Unit
			Min.	Typ.	Max.	
Thermal resistance ( 1 device )	R <sub>th(j-c)</sub>	Inverter IGBT			0.63	°C/W
		Inverter FWD			1.33	
		Brake IGBT			1.04	
		Thyristor			1.00	
		Converter Diode			0.90	
Contact thermal resistance *	R <sub>th(c-f)</sub>	With thermal compound		0.05		

\* This is the value which is defined mounting on the additional cooling fin with thermal compound

## ■ Outline Drawings, mm



## ■ Equivalent Circuit Schematic

